



THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION OF

SHIBATA

Appln. No.: 09/493,819

Filed: January 28, 2000

Title: GROUP III NITRIDE COMPOUND SEMICONDUCTOR DEVICE

Confirmation No.:

Group Art Unit: 2814

Examiner: D. WILLE

October 12, 2001

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AMENDMENT UNDER 37 C.F.R. § 1.111

Hon. Commissioner of Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated July 12, 2001, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 2 without prejudice.

Please amend claim 1 as follows:

1. (Amended) A group III nitride compound semiconductor device of a successively laminated structure comprising:

a substrate;

a buffer layer;

a first layer formed of $\text{In}_x\text{Ga}_{1-x}\text{N}$ ($0 < x < 1$); and

a second layer formed of $\text{In}_y\text{Ga}_{1-y}\text{N}$ ($0 < y < 1$, $y \neq x$);